

N-Channel Enhancement Mode Field Effect Transistor (7.2A, 30V, 0.035Ω) (N-channel enhancement type field effect transistor (drain current 7.2A, drain-source voltage of 30V, resistance 0.035Ω)), MOSFET N-Channel FET Enhancement Mode

Manufacturers	<u>ON Semiconductor, LLC</u>
Package/Case	SOT-223
Product Type	Transistors
RoHS	Rohs
Lifecycle	



Images are for reference only

Please submit RFQ for NDT451AN or [Email to us: sales@ovaga.com](mailto:sales@ovaga.com) We will contact you in 12 hours.

RFQ

General Description

Power SOT N-Channel enhancement mode power field effect transistors are produced using Fairchild's proprietary, high cell density, DMOS technology. This very high density process is especially tailored to minimize on-state resistance and provide superior switching performance. These devices are particularly suited for low voltage applications such as DC motor control and DC/DC conversion where fast switching, low in-line power loss, and resistance to transients are needed.

Features

7.2A, $V_{GS} = 4.5V$

High density cell design for extremely low RDS(ON)

High power and current handling capability in a widely used surface mount package

Application

ONSEMI

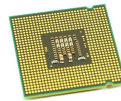


Related Products



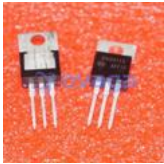
[NDS9945](#)

ON Semiconductor, LLC
SOP-8



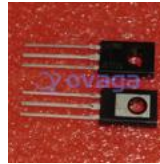
[NTND31225CZTAG](#)

ON Semiconductor, LLC
XLLGA-6



[D45H11G](#)

ON Semiconductor, LLC
TO-220



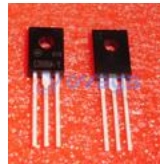
[MJE172](#)

ON Semiconductor, LLC
TO-126



[MJE350G](#)

ON Semiconductor, LLC
TO-126



[KSC2690AYSTU](#)

ON Semiconductor, LLC
TO-126



[2SC4027S-TL-E](#)

ON Semiconductor, LLC
TO-252



[NTR4003NT3G](#)

ON Semiconductor, LLC
SOT-23